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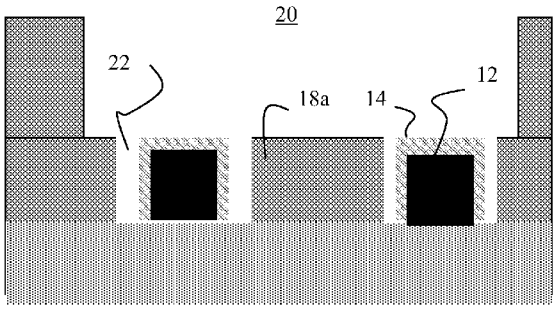
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FIG. 6




(57) Abstract: A MUGFET and method of manufacturing a MUGFET is shown. The method of manufacturing the MUGFET includes forming temporary spacer gates (16 of FIG. 6) about a plurality of active regions and depositing a dielectric material (18a and in space 20) over the temporary spacer gates, including between the plurality of active regions. The method further includes etching portions of the dielectric material (20) to expose the temporary spacer gates (16) and removing the temporary spacer gates, leaving a space between the active regions and a remaining portion of the dielectric material (18a). The method additionally includes filling the space (20) between the active regions and above the remaining portion of the dielectric material (18a) with a gate material.

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